

TD62783APG, TD62783AFG, TD62784APG, TD62784AFG

8 ch High-Voltage Source Driver

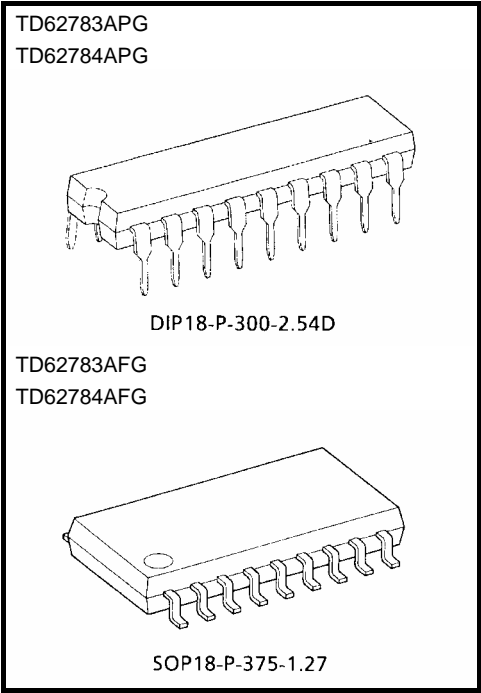
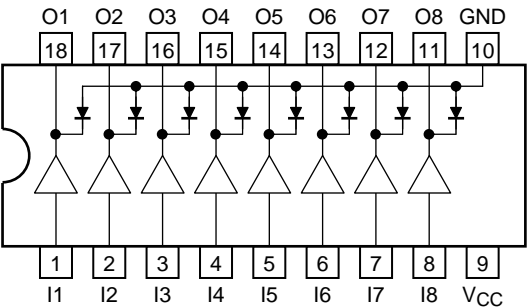
The TD62783APG/AFG Series are comprised of eight source current Transistor Array.  
These drivers are specifically designed for fluorescent display applications.  
Applications include relay, hammer and lamp drivers.

Features

- High output voltage:  $V_{CC} = 50\text{ V (min)}$
- Output current (single output):  $I_{OUT} = -500\text{ mA (min)}$
- Output clamp diodes
- Single supply voltage
- Input compatible with various types of logic
- Package type-APG: DIP-18 pin
- Package type-AFG: SOP-18 pin

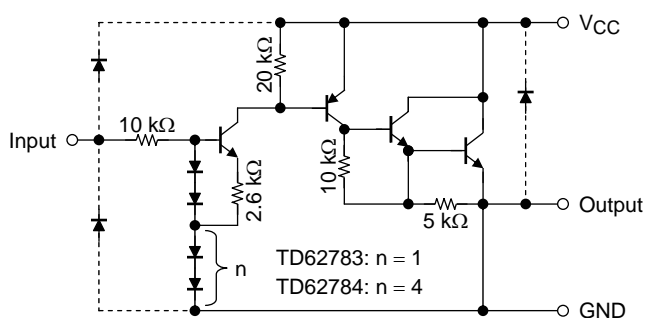
Type	Designation
TD62783APG/AFG	TTL, 5V CMOS
TD62784APG/AFG	6 to 15V PMOS, CMOS

Pin Assignment (top view)



Weight  
DIP18-P-300-2.54D: 1.47 g (typ.)  
SOP18-P-375-1.27: 0.41 g (typ.)

### Schematics (each driver)



Note: The input and output parasitic diodes cannot be used as clamp diodes.

### Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Supply voltage		V <sub>CC</sub>	50	V
Output current		I <sub>OUT</sub>	−500	mA/ch
Input voltage		V <sub>IN</sub> (Note 1)	15	V
		V <sub>IN</sub> (Note 2)	30	
Clamp diode reverse voltage		V <sub>R</sub>	50	V
Clamp diode forward current		I <sub>F</sub>	500	mA
Power dissipation	APG	P <sub>D</sub> (Note 3)	1.47	W
	AFG		0.96	
Operating temperature		T <sub>opr</sub>	−40 to 85	°C
Storage temperature		T <sub>stg</sub>	−55 to 150	°C

Note 1: Only TD62783APG/AFG

Note 2: Only TD62784APG/AFG

Note 3: Delated above 25°C in the proportion of 11.7 W/°C (APG type), 7.7 W/°C (AFG type)

## Recommended Operating Conditions (Ta = -40 to 80°C)

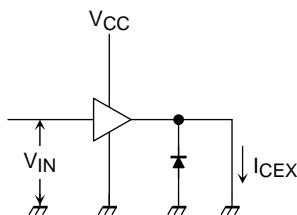
Characteristics			Symbol	Test Condition		Min	Typ.	Max	Unit
Supply voltage			V <sub>CC</sub>	—		—	—	50	V
Output current		AFG	I <sub>OUT</sub>	Ta = 85°C, T <sub>j</sub> = 120°C, T <sub>pw</sub> = 25 ms	Duty = 10% 8 circuits	—	—	−260	mA/ch
					Duty = 50% 8 circuits	—	—	−59	
					Duty = 10% 8 circuits	—	—	−180	
					Duty = 50% 8 circuits	—	—	−38	
Input voltage		TD62783APG/AFG	V <sub>IN</sub>	—		—	—	12	V
		TD62784APG/AFG		—		—	—	24	
Input voltage	Output ON	TD62783APG/AFG	V <sub>IN</sub> (ON)	—		20	50	15	V
		TD62784APG/AFG	V <sub>IN</sub> (OFF)	—		4.5	12.0	30	
	Output OFF	TD62783APG/AFG		—		0	—	0.8	
		TD62784APG/AFG		—		0	—	2.0	
Clamp diode reverse voltage		APG	V <sub>R</sub>	—		—	—	50	V
		AFG		—		—	—	35	
Clamp diode forward current			I <sub>F</sub>	—		—	—	400	mA
Power dissipation		APG	P <sub>D</sub>	—		—	—	0.52	W
		AFG		—		—	—	0.35	

## Electrical Characteristics (Ta = 25°C)

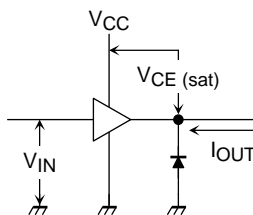
Characteristics		Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Output leakage current		I <sub>CEX</sub>	1	V <sub>CC</sub> = V <sub>CC</sub> max V <sub>IN</sub> = 0.4 V Ta = 25°C	—	—	100	μA
Output saturation voltage		V <sub>CE</sub> (sat)	2	V <sub>IN</sub> = V <sub>IN</sub> (ON), I <sub>OUT</sub> = -350 mA	—	—	2.0	V
				V <sub>IN</sub> = V <sub>IN</sub> (ON), I <sub>OUT</sub> = -225 mA	—	—	1.9	
				V <sub>IN</sub> = V <sub>IN</sub> (ON), I <sub>OUT</sub> = -100 mA	—	—	1.8	
Input current	TD62783APG/AFG	I <sub>IN</sub> (ON)	3	V <sub>IN</sub> = 2.4 V	—	36	52	μA
	TD62784APG/AFG			V <sub>IN</sub> = 3.85 V	—	180	260	
				V <sub>IN</sub> = 5 V	—	92	130	
				V <sub>IN</sub> = 12 V	—	790	1130	
Input voltage	TD62783APG/AFG	V <sub>IN</sub> (ON)	4	V <sub>CE</sub> = 2.0 V	—	—	2.0	V
	TD62784APG/AFG			I <sub>OUT</sub> = -350 mA	—	—	4.5	
	TD62783APG/AFG	V <sub>IN</sub> (OFF)		I <sub>OUT</sub> = -500 μA	0.8	—	—	
	TD62784APG/AFG				2.0	—	—	
Supply current		I <sub>CC</sub> (ON)	3	V <sub>IN</sub> = V <sub>IN</sub> (ON), V <sub>CC</sub> = 50 V	—	—	2.5	mA/ch
Clamp diode reverse current		I <sub>R</sub>	5	V <sub>R</sub> = 50 V	—	—	50	μA
Clamp diode forward voltage		V <sub>F</sub>	6	I <sub>F</sub> = 350 mA	—	—	2.0	V
Turn-ON delay		t <sub>ON</sub>	7	V <sub>CC</sub> = V <sub>CC</sub> max R <sub>L</sub> = 125 Ω C <sub>L</sub> = 15 pF, R <sub>L</sub> = 88 Ω	—	0.15	—	μs
Turn-OFF delay		t <sub>OFF</sub>	7	V <sub>CC</sub> = V <sub>CC</sub> max R <sub>L</sub> = 125 Ω C <sub>L</sub> = 15 pF, R <sub>L</sub> = 88 Ω	—	1.8	—	μs

## Test Circuit

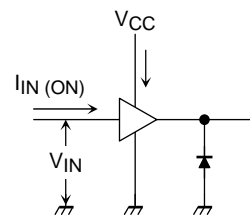
### 1. $I_{CEX}$



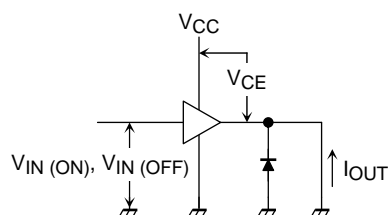
### 2. $V_{CE(sat)}$



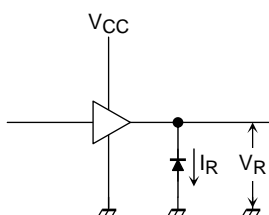
### 3. $I_{IN(ON)}$ , $I_{CC}$



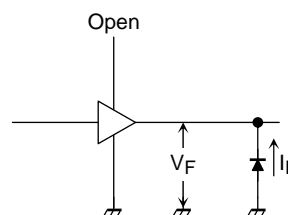
### 4. $V_{IN(ON)}$ , $V_{IN(OFF)}$



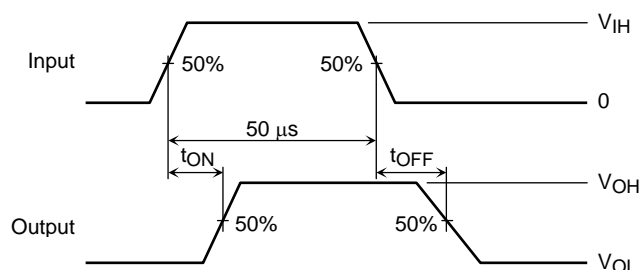
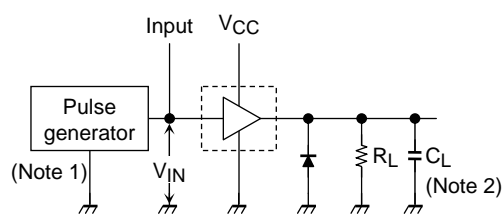
### 5. $I_R$



### 6. $V_F$



### 7. $t_{ON}$ , $t_{OFF}$



Note 1: Pulse Width 50  $\mu$ s, Duty Cycle 10%  
Output Impedance 50  $\Omega$ ,  $t_r \leq 5$  ns,  $t_f \leq 10$  ns

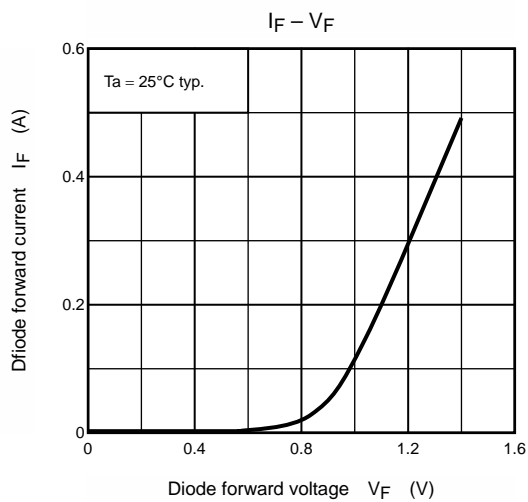
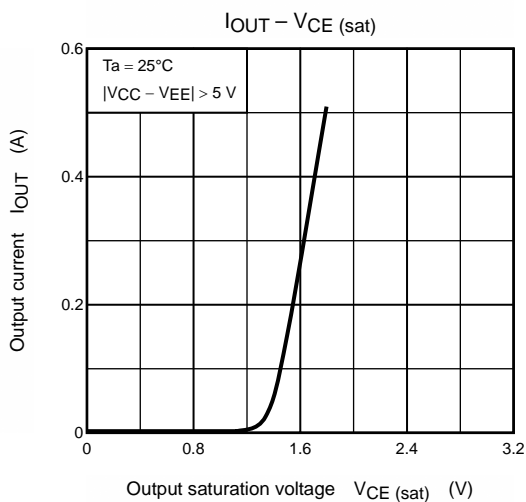
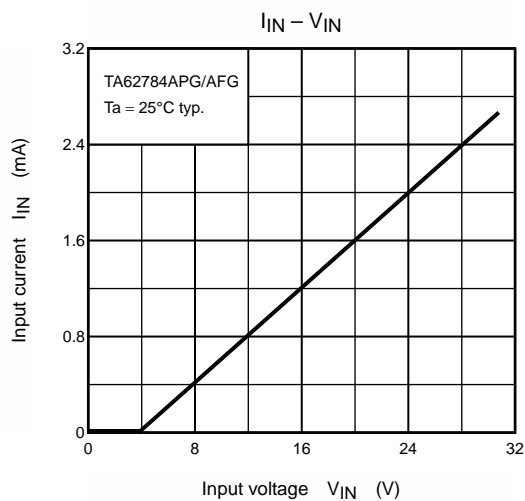
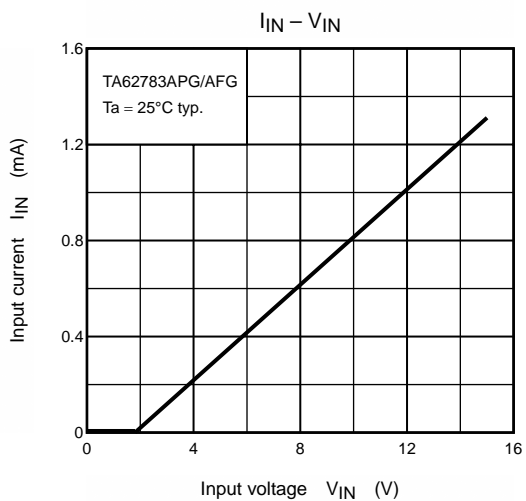
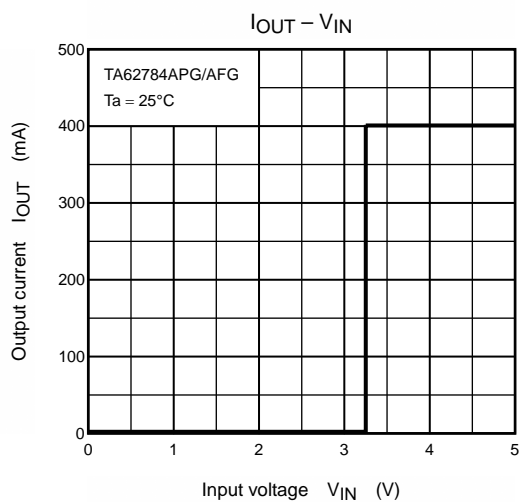
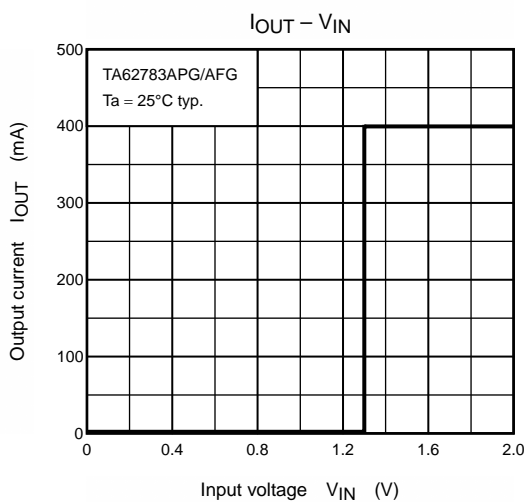
Note 2:  $C_L$  includes probe and jig capacitance.

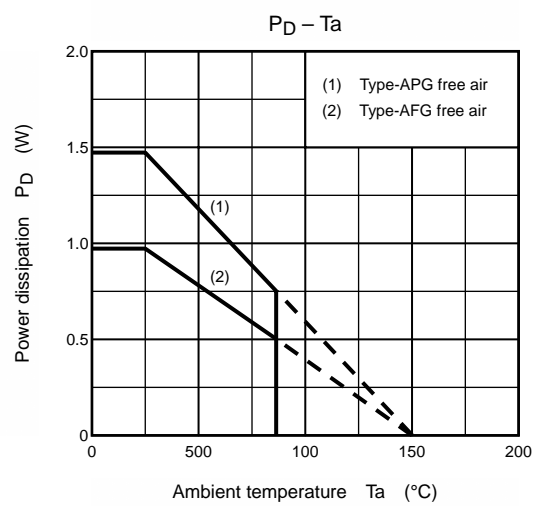
## Precautions for Using

This IC does not integrate protection circuits such as overcurrent and overvoltage protectors.

Thus, if excess current or voltage is applied to the IC, the IC may be damaged. Please design the IC so that excess current or voltage will not be applied to the IC.

Utmost care is necessary in the design of the output line,  $V_{CC}$  and GND line since IC may be destroyed due to short-circuit between outputs, air contamination fault, or fault by improper grounding.

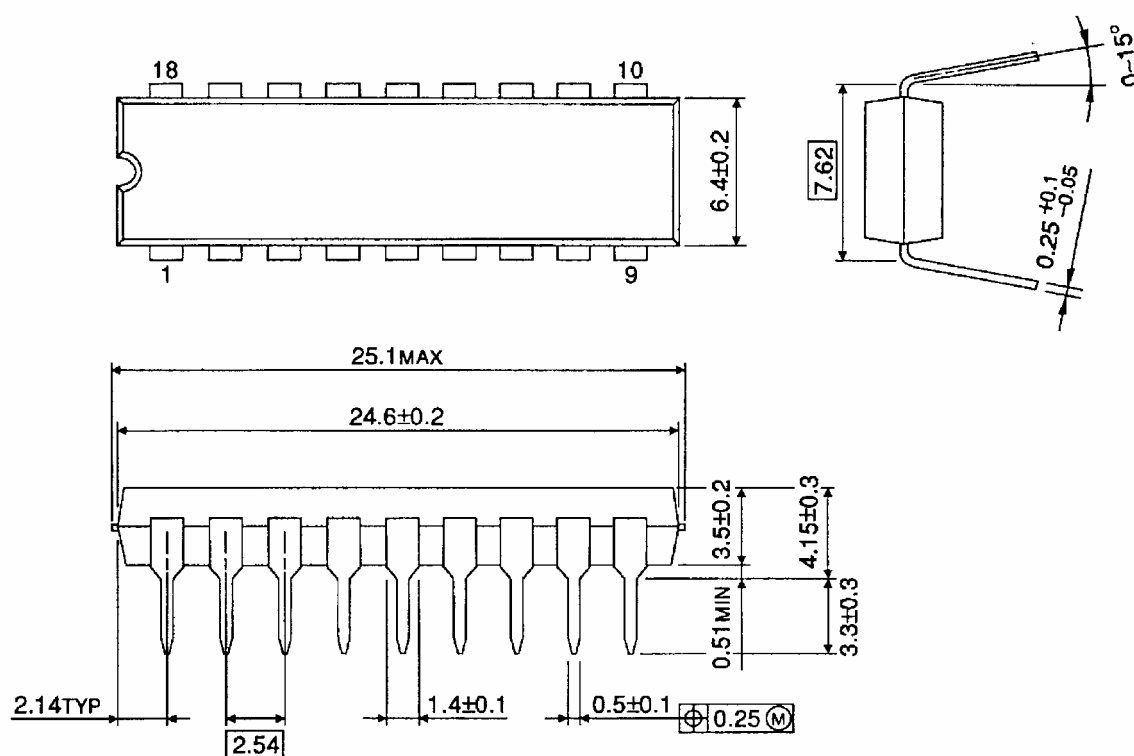




## Package Dimensions

DIP18-P-300-2.54D

Unit : mm

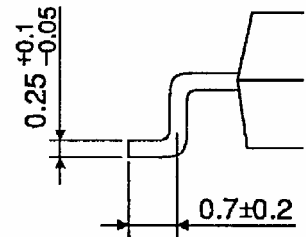
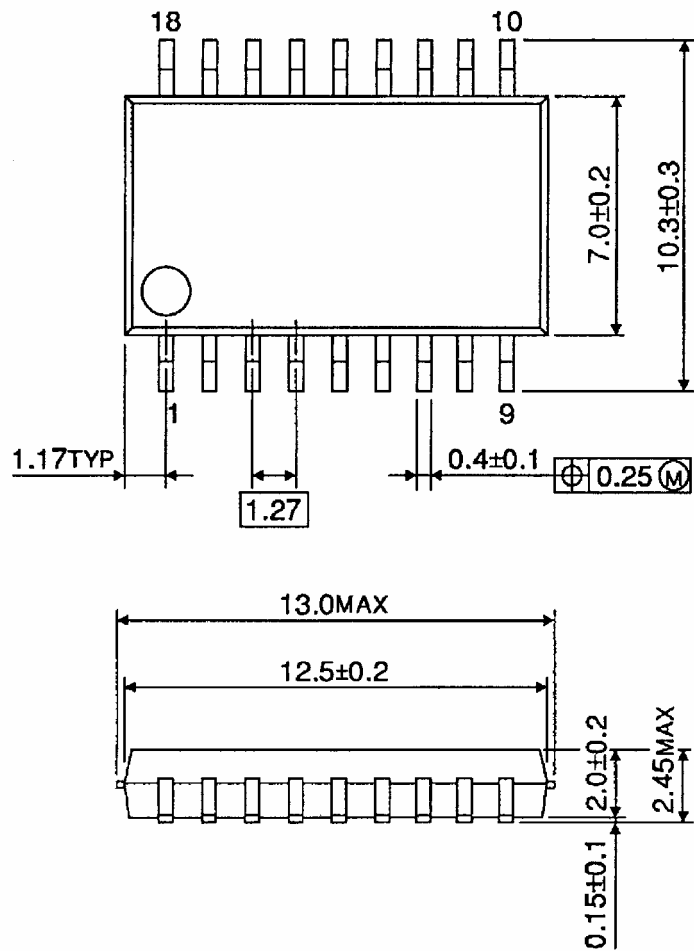


Weight: 1.47 g (typ.)

Package Dimensions

SOP18-P-375-1.27

Unit : mm



Weight: 0.41 g (typ.)



About solderability, following conditions were confirmed

- Solderability

- (1) Use of Sn-63Pb solder Bath

- solder bath temperature = 230°C
    - dipping time = 5 seconds
    - the number of times = once
    - use of R-type flux

- (2) Use of Sn-3.0Ag-0.5Cu solder Bath

- solder bath temperature = 245°C
    - dipping time = 5 seconds
    - the number of times = once
    - use of R-type flux

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